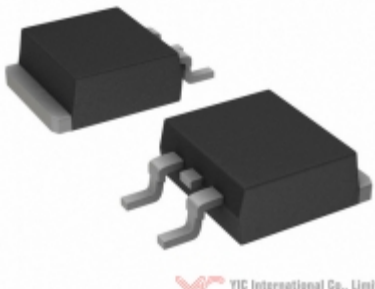









	<h2 style="color: red;">FQB630TM</h2>
 <p>Image may be representation. See specs for product details.</p>	Hersteller-Teilenummer: FQB630TM
	Hersteller / Marke: AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung: MOSFET N-CH 200V 9A D2PAK
	Datenblätter:  FQB630TM.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 5000 pcs Stock Available.
	Liefern von: Hong Kong
Versandweg: DHL/Fedex/TNT/UPS/EMS	

Spezifikationen

Teilenummer	FQB630TM
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 200V 9A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	5000 pcs Stock
detaillierte Beschreibung	N-Channel 200V 9A (Tc) 3.13W (Ta), 78W (Tc) Surface
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 78W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	200V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	9A (Tc)
Rds On (Max) @ Id, Vgs	400 mOhm @ 4.5A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	25nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	550pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±25V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)


















































FQB630TM ist neu im Original, Suche FQB630TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB630TM AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB630TM: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQB65N06TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 65A D2PAK</p>	 <p>FQB60N03LTM FSC FSC TO-263</p>	 <p>FQB6035AL FSC FSC TO-263</p>	 <p>FQB5P20TM Fairchild/ON Semiconductor MOSFET P-CH 200V 4.8A D2PAK</p>
 <p>FQB65N06 FAIRCHI FQB65N06 FAIRCHI</p>	 <p>FQB630TM Fairchild/ON Semiconductor MOSFET N-CH 200V 9A D2PAK</p>	 <p>FQB6N15TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 150V 6.4A D2PAK</p>	 <p>FQB5P20TMX Fairchild/ON Semiconductor FQB5P20TMX FAIRCHILD</p>

heiße Teile

Mehr

 FQB50N06L	 FQB50N06LTM	 FQB50N06LTM	 FQB50N06M	 FQB50N06TM
 FQB50N06TM	 FQB50N06TM-NL	 FQB55N06TM	 FQB55N06TM	 FQB55N10
 FQB55N10TM	 FQB55N10TM	 FQB5N20L	 FQB5N30TM	 FQB5N30TM
 FQB5N50C	 FQB5N50CF	 FQB5N50CTM	 FQB5N50CTM	 FQB5N60CTM
 FQB5N60CTM	 FQB5N90TM	 FQB5N90TM	 FQB5P10TM	 FQB5P10TM
 FQB630TM	 FQB65N06	 FQB65N06TM	 FQB65N06TM	 FQB6N40C
 FQB6N40CF	 FQB6N40CTM	 FQB6N40CTM	 FQB6N50TM	 FQB6N50TM
 FQB6N60C	 FQB6N60CTM	 FQB6N60CTM	 FQB6N60TM	 FQB6N60TM
 FQB6N70TM	 FQB6N70TM	 FQB6N90TM	 FQB6N90TM_AM002	 FQB6N90TM_AM002
 FQB7042FB	 FQB7045FB	 FQB70N03	 FQB70N06	 FQB70N08

Contact us: Info@Y-IC.com

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